	Application No.	Applicant(s)	
Notice of Allewshillts	10/777,233	SHIN ET AL	
Notice of Allowability	Examiner	Art Unit	
	William M. Brewster	2823	
The MAILING DATE of this communication appears on the cover sheet with the correspondence address All claims being allowable, PROSECUTION ON THE MERITS IS (OR REMAINS) CLOSED in this application. If not included herewith (or previously mailed), a Notice of Allowance (PTOL-85) or other appropriate communication will be mailed in due course. THIS NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT RIGHTS. This application is subject to withdrawal from issue at the initiative of the Office or upon petition by the applicant. See 37 CFR 1.313 and MPEP 1308.			
1. This communication is responsive to <u>28 April 2005</u> .			
2. The allowed claim(s) is/are <u>4-6,8 and 9</u> .			
3. The drawings filed on 11 February 2004 are accepted by the Examiner.			
<ul> <li>4.</li></ul>			
Attachment(s)  1. ☑ Notice of References Cited (PTO-892)  2. ☐ Notice of Draftperson's Patent Drawing Review (PTO-948)  3. ☐ Information Disclosure Statements (PTO-1449 or PTO/SB/0: Paper No./Mail Date  4. ☐ Examiner's Comment Regarding Requirement for Deposit of Biological Material	5. Notice of Informal Page 1  Notice of Informal Page 1  No./Mail Date 2  No./Mail Date 3  Notice 2  Notic	(PTO-413), e nent/Comment	ŕ

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## **EXAMINER'S AMENDMENT**

An examiner's amendment to the record appears below. Should the changes and/or additions be unacceptable to applicant, an amendment may be filed as provided by 37 CFR 1.312. To ensure consideration of such an amendment, it MUST be submitted no later than the payment of the issue fee.

The application has been amended as follows:

a) In the Title

After "Same", insert --Including Forming Metal Silicide Gate Lines and Source Lines--

## **Reasons for Allowances**

The following is an examiner's statement of reasons for allowance: in claim 8, lines 7-19, the features including forming a floating gate, control gate, etching a groove in the interlayer insulating layer over the source, depositing silicon layer to fill the groove, planarizing the silicon layer and ILD, and forming a metal silicide on the exposed gate lines and common source line cannot be reasonably combined from the prior art of record. The prior art of record fails to teach, in combination, the process features.

Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance."

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Any inquiry concerning this communication or earlier communications from the examiner should be directed to William M. Brewster whose telephone number is 571-272-1854. The examiner can normally be reached on Full Time.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Olik Chaudhuri can be reached on 571-272-1855. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

6 May 2005

William M. Brouster

**WB**